
2SK1215

Silicon N-Channel MOS FET

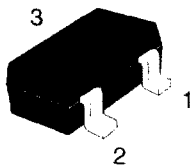
HITACHI

Application

VHF amplifier

Outline

CMPAK



1. Gate
2. Drain
3. Source

2SK1215

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSX}^{*1}	20	V
Gate to source voltage	V_{GS}	±5	V
Drain current	I_D	30	mA
Gate current	I_G	±1	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. $V_{GS} = -4$ V

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	20	—	—	V	$I_D = 100 \mu A, V_{GS} = -4$ V
Gate cutoff current	I_{GSS}	—	—	±20	nA	$V_{GS} = \pm 5$ V, $V_{DS} = 0$
Drain current	I_{DSS}^{*1}	4	—	12	mA	$V_{DS} = 10$ V, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0	—	-2.0	V	$V_{DS} = 10$ V, $I_D = 10 \mu A$
Forward transfer admittance	$ y_{fs} $	8	14	—	mS	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ kHz
Input capacitance	Ciss	—	2.5	—	pF	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ MHz
Output capacitance	Coss	—	1.6	—	pF	
Reverse transfer capacitance	Crss	—	0.03	—	pF	
Power gain	PG	24	—	—	dB	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 100$ MHz
Noise figure	NF	—	—	3	dB	

Note: 1. The 2SK1215 is grouped by I_{DSS} as follows.

Grade	D	E	F
Mark	IGD	IGE	IGF
I_{DSS}	4 to 8	6 to 10	8 to 12

See characteristic curves of 2SK359.